

Radiation Hardened Uncompensated, High Slew Rate Operational Amplifier

The HS-2520RH is a radiation hardened monolithic operational amplifier which delivers an unsurpassed combination of specifications for slew rate, bandwidth and settling time. This dielectrically isolated amplifier is designed for closed loop gains of 3 or greater without external compensation. In addition, this high performance component also provides low offset current and high input impedance.

The 100V/μs (Min) slew rate and fast settling time of this amplifier makes it an ideal component for pulse amplification and data acquisition designs. To insure compliance with slew rate and transient response specifications, all devices are 100% tested for AC performance characteristics over full temperature. This device is a valuable component for RF and video circuitry requiring wideband operation. For accurate signal conditioning designs, the HS-2520RH superior dynamic specifications are complemented by 25nA (Max) offset current and offset voltage trim capability.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95685. A "hot-link" is provided on our homepage for downloading.
www.intersil.com/spacedefense/space.asp

Features

- Electrically Screened to SMD # 5962-95685
- QML Qualified per MIL-PRF-38535 Requirements
- High Slew Rate 100V/μs Min, 120V/μs (Typ)
- Wide Power Bandwidth 1.5MHz (Min)
- Wide Gain Bandwidth 10MHz Min, 20MHz (Typ)
- High Input Impedance 50MΩ Min, 100MΩ (Typ)
- Low Offset Current 25nA Min, 10nA (Typ)
- Fast Settling (0.1% of 10V Step) 200ns (Typ)
- Low Quiescent Supply Current 6mA (Max)
- Gamma Dose 1 x 10⁴RAD(Si)

Applications

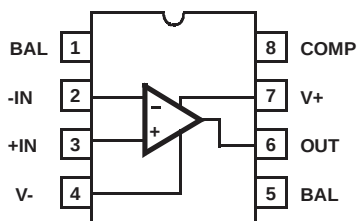
- Data Acquisition Systems
- RF Amplifiers
- Video Amplifiers
- Signal Generators
- Pulse Amplifiers

Ordering Information

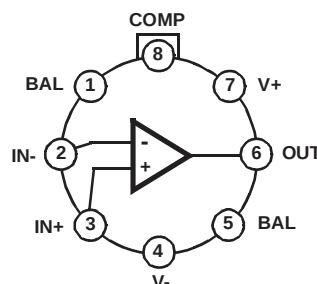
ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
HS0-2520RH-Q	HS0-2520RH-Q	25
5962D9568501VGA	HS2-2520RH-Q	-55 to 125
5962D9568501VPA	HS7-2520RH-Q	-55 to 125
5962D9568501VPC	HS7B-2520RH-Q	-55 to 125

Pinouts

**HS7-2520RH (CERDIP) GDIP1-T8
OR
HS7B-2520RH (SBDIP) CDIP2-T8
TOP VIEW**



**HS2-2520RH (CAN) MACY1-X8
TOP VIEW**



Timing Waveforms

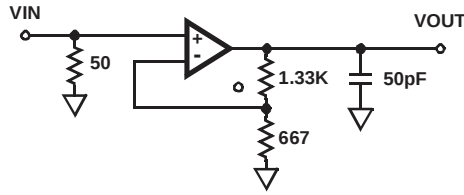


FIGURE 1. SIMPLIFIED TEST CIRCUIT

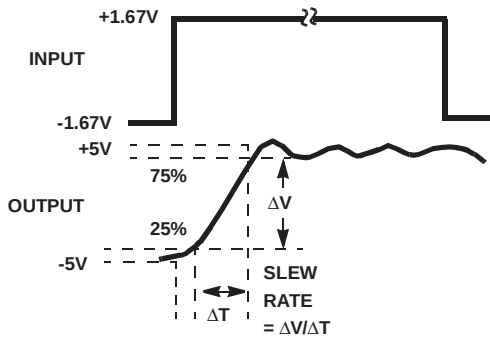


FIGURE 2. SLEW RATE WAVEFORM

NOTE: Measured on both positive and negative transitions. Capacitance at Compensation pin should be minimized.

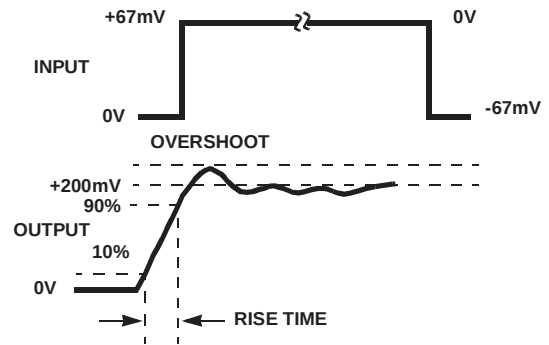


FIGURE 3. TRANSIENT RESPONSE WAVEFORM

Typical Performance Curves $T_A = 25^{\circ}\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$, Unless Otherwise Specified

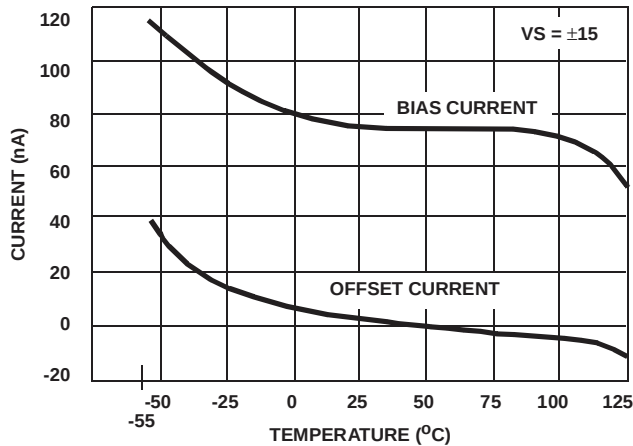


FIGURE 4. INPUT BIAS AND OFFSET CURRENT vs TEMPERATURE

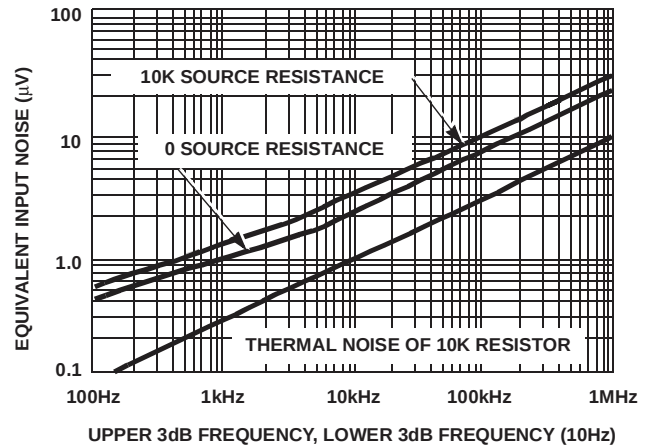


FIGURE 5. EQUIVALENT INPUT NOISE vs BANDWIDTH

Typical Performance Curves $T_A = 25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$, Unless Otherwise Specified (Continued)

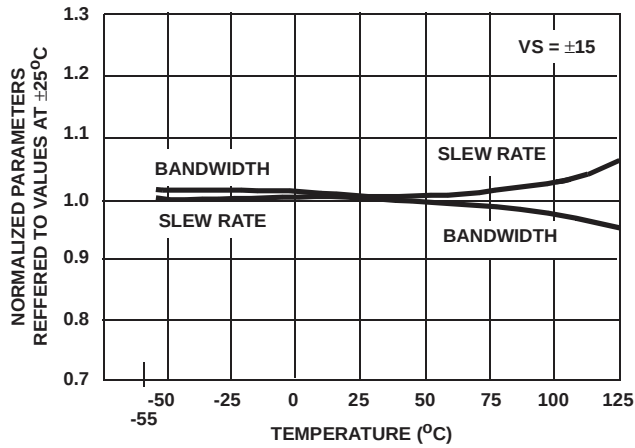


FIGURE 6. NORMALIZED AC PARAMETERS vs TEMPERATURE

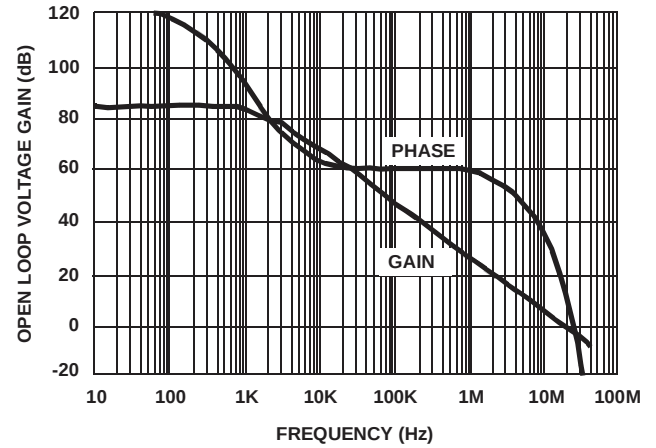


FIGURE 7. OPEN-LOOP FREQUENCY AND PHASE RESPONSE

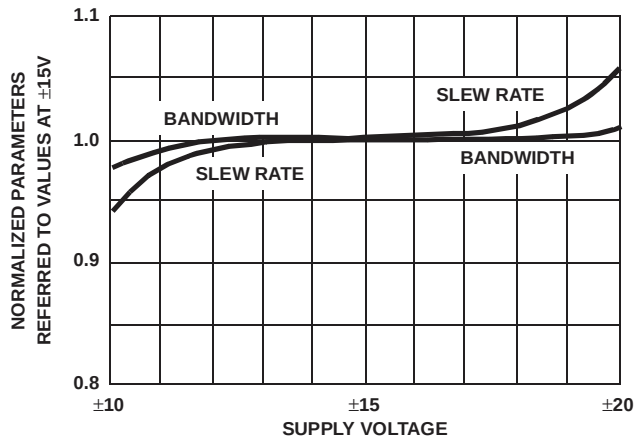


FIGURE 8. NORMALIZED AC PARAMETERS vs SUPPLY VOLTAGE AT 25°C

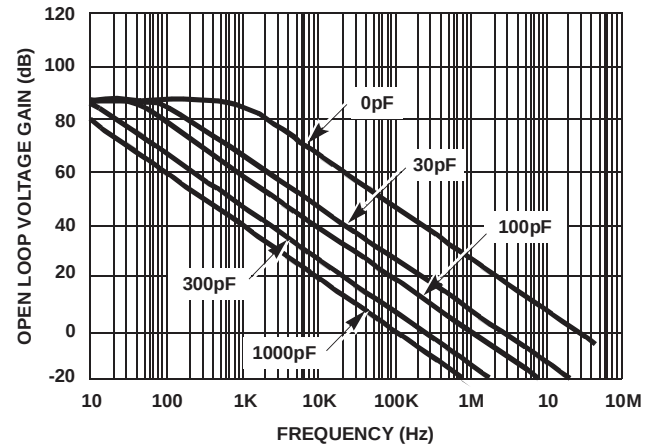


FIGURE 9. OPEN-LOOP FREQUENCY RESPONSE FOR VARIOUS VALUES OF CAPACITORS FROM BANDWIDTH CONTROL PIN TO GROUND

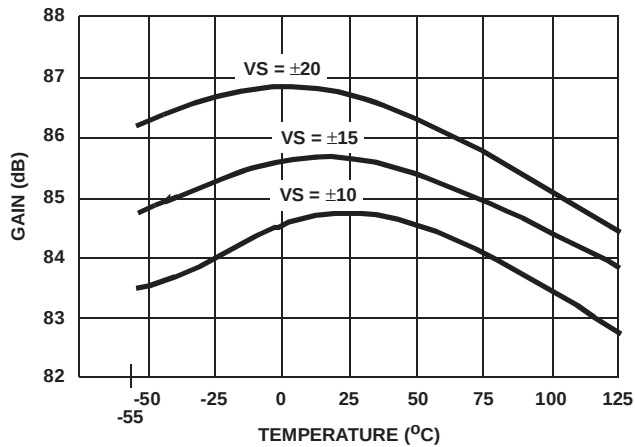


FIGURE 10. OPEN-LOOP VOLTAGE GAIN vs TEMPERATURE

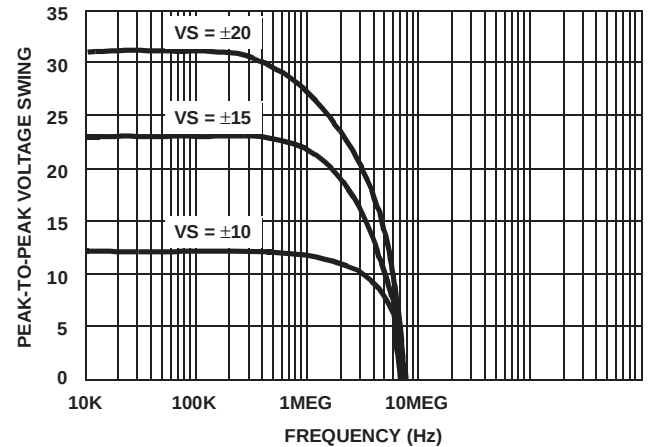


FIGURE 11. OUTPUT VOLTAGE SWING vs FREQUENCY AT 25°C

Typical Performance Curves $T_A = 25^\circ\text{C}$, $V_{\text{SUPPLY}} = \pm 15\text{V}$, Unless Otherwise Specified (Continued)

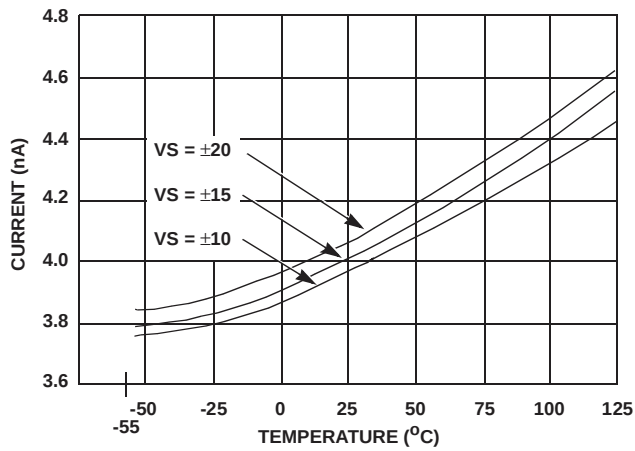


FIGURE 12. POWER SUPPLY CURRENT vs TEMPERATURE

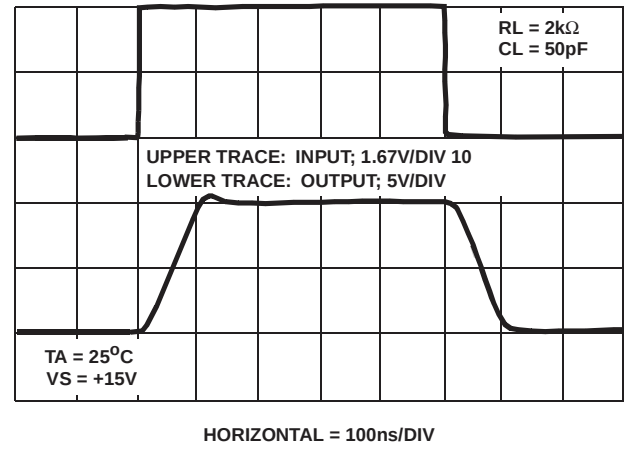


FIGURE 13. VOLTAGE FOLLOWER PULSE RESPONSE

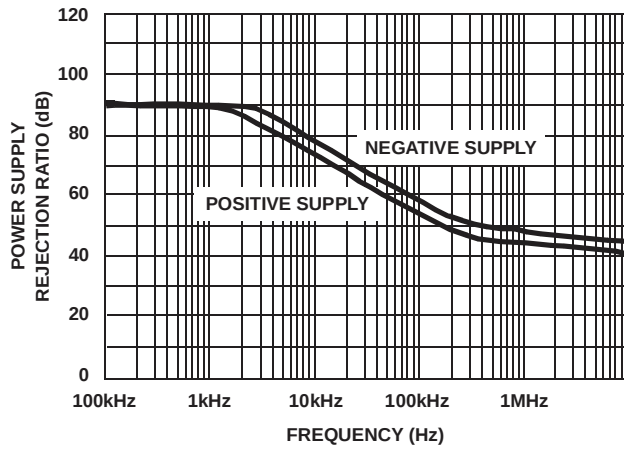


FIGURE 14. POWER SUPPLY REJECTION RATIO vs FREQUENCY

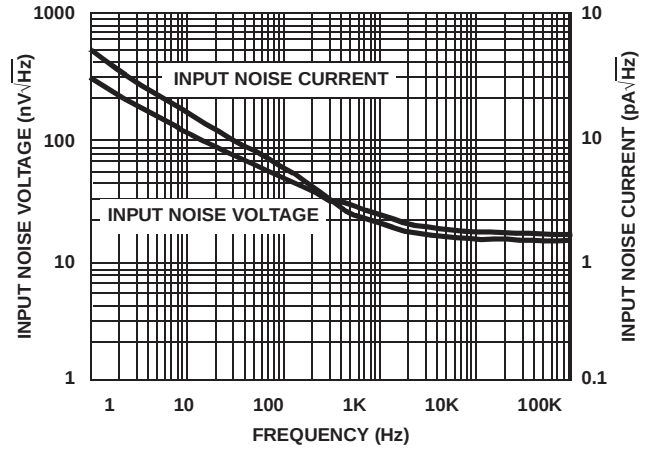
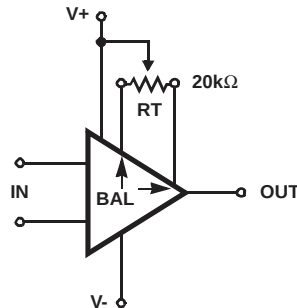


FIGURE 15. INPUT NOISE DENSITY vs FREQUENCY

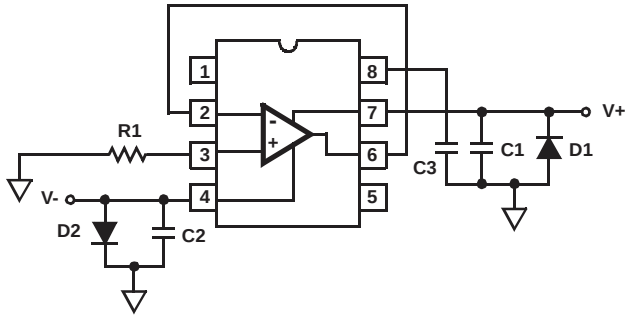
Suggested VOS Adjustment



NOTE: Tested offset adjustment range is $|V_{\text{OS}} + 1\text{mV}|$ minimum referred to output. Typical range is $+20\text{mV}$ to -18mV with $R_T = 20\text{k}\Omega$.

Burn-In Circuits

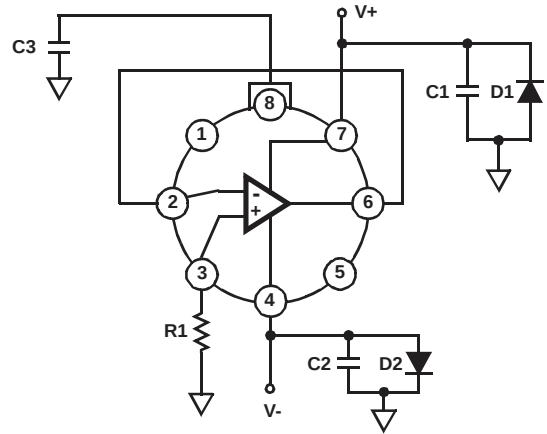
HS7-2520 CERDIP



NOTES:

1. $R1 = 1M\Omega$, $\pm 5\%$, 1/4W (Min)
2. $C1 = C2 = 0.01\mu F$ /Socket (Min) or $0.1\mu F$ /Row (Min)
3. $C3 = 0.01\mu F$ ($\pm 10\%$)/Socket
4. $D1 = D2 = 1N4002$ or equivalent (per board)
5. $|(V+) - (V-)| = 31V$

HS2-2520 METAL CAN

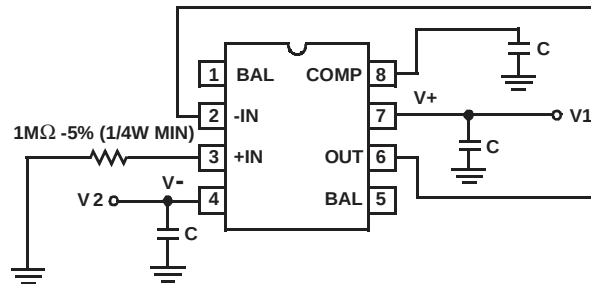


NOTES:

6. $R1 = 1M\Omega$, $\pm 5\%$, 1/4W (Min)
7. $C1 = C2 = 0.01\mu F$ /Socket (Min) or $0.1\mu F$ /Row (Min)
8. $C3 = 0.01\mu F$ ($\pm 10\%$)/Socket
9. $D1 = D2 = 1N4002$ or equivalent (per board)
10. $|(V+) - (V-)| = 31V$

Irradiation Circuits

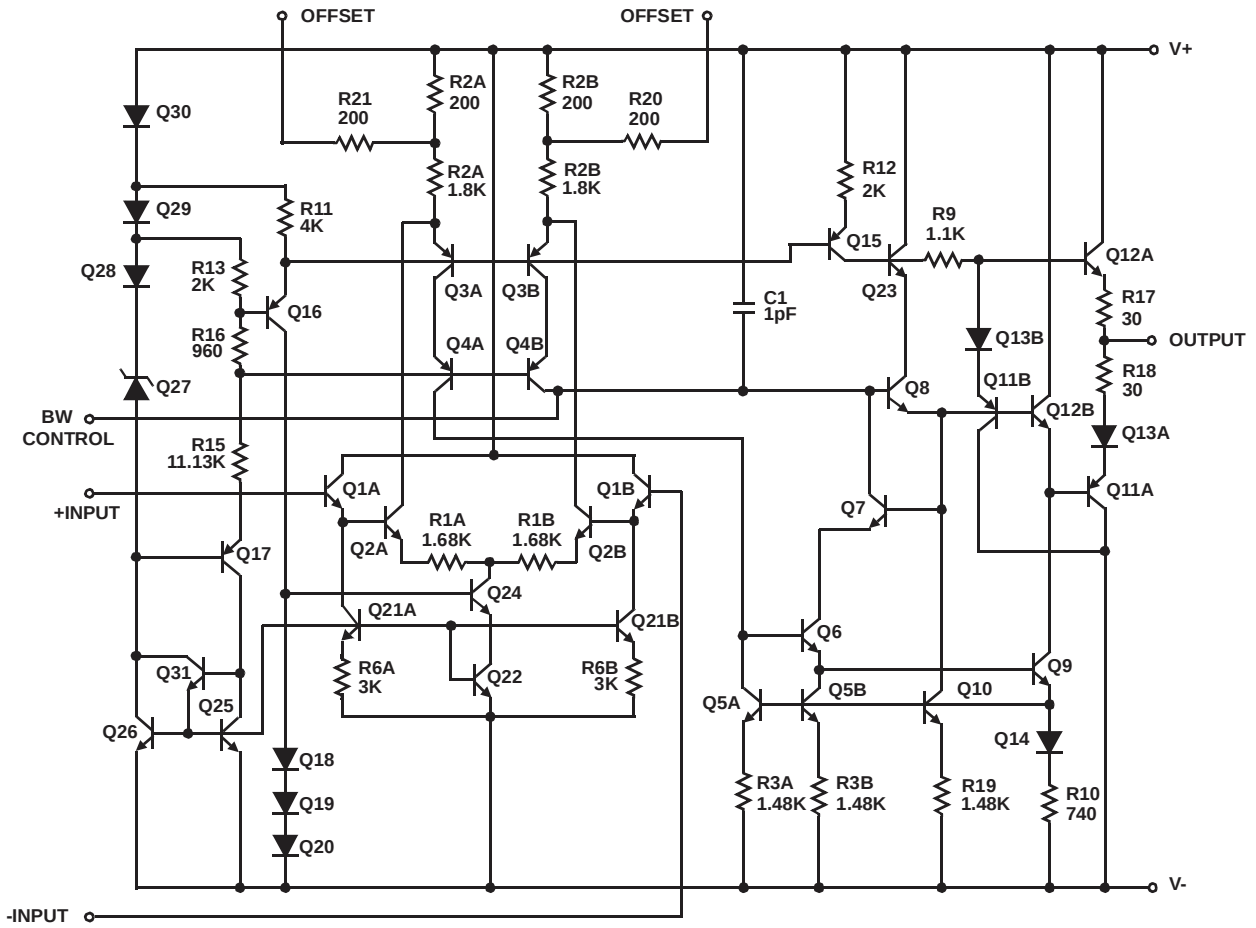
IRRADIATION CIRCUIT



NOTES:

11. $V1 = +15V \pm 10\%$
12. $V2 = -15V \pm 10\%$
13. $C = 0.1\mu F \pm 10\%$

Schematic Diagram



Die Characteristics

DIE DIMENSIONS:

67 mils x 57 mils x 19 mils
(1700μm x 1440μm x 483μm)

INTERFACE MATERIALS:

Glassivation:

Type: Nitride (Si₃N₄) over Silox (SiO₂, 5% Phos.)
Silox Thickness: 12kÅ ±2kÅ
Nitride Thickness: 3.5kÅ ±1.5kÅ

Top Metallization:

Type: Al, 1% Cu
Thickness: 16kÅ ±2kÅ

Substrate:

Bipolar Dielectric Isolation

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION:

Substrate Potential (Powered Up):

Unbiased

ADDITIONAL INFORMATION:

Worst Case Current Density:

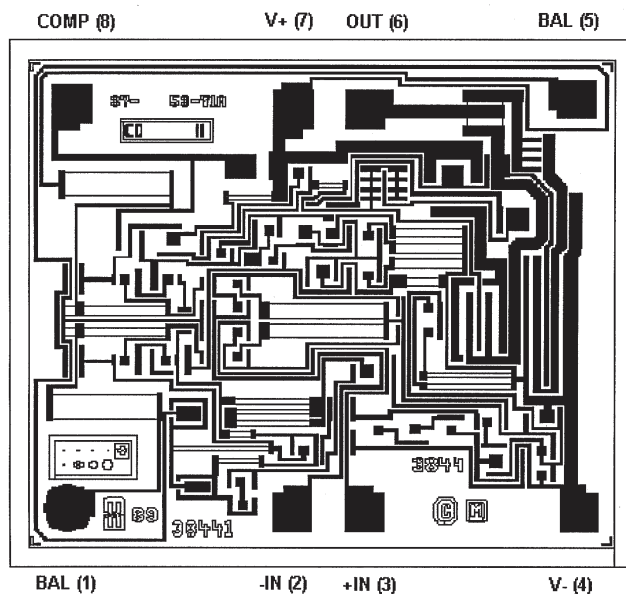
$0.26 \times 10^5 \text{ A/cm}^2$

Transistor Count:

40

Metallization Mask Layout

HS-2520RH



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